

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2024/0213159 A1 Parbatani et al.

(43) **Pub. Date:**

Jun. 27, 2024

(54) GRAPHENE-CAPPED COPPER IN DUAL DAMASCENE INTERCONNECT

(71) Applicant: Lam Research Corporation, Fremont, CA (US)

(72) Inventors: Asish Parbatani, Albany, NY (US); Bart J. van Schravendijk, Palo Alto, CA (US); Bhadri N. Varadarajan, Beaverton, OR (US); Ieva Narkeviciute, Portland, OR (US); Easwar Srinivasan, Portland, OR (US); Kashish Sharma, Tigard, OR (US); Randolph Knarr, Voorheesville, NY (US); Stefan Schmitz, Malta, NY (US); Vinayak Ramanan, Portland, OR (US)

18/291,200 (21) Appl. No.: (22) PCT Filed: Jul. 19, 2022

(86) PCT No.: PCT/US2022/073906

§ 371 (c)(1),

(2) Date: Jan. 22, 2024

Related U.S. Application Data

(60) Provisional application No. 63/203,480, filed on Jul. 23, 2021.

Publication Classification

(51)	Int. Cl.	
	H01L 23/532	(2006.01)
	C23C 16/04	(2006.01)
	C23C 16/26	(2006.01)
	C23C 16/455	(2006.01)
	C23C 16/56	(2006.01)
	H01L 21/768	(2006.01)

(52) U.S. Cl. CPC H01L 23/53276 (2013.01); C23C 16/04 (2013.01); C23C 16/26 (2013.01); C23C 16/45525 (2013.01); C23C 16/56 (2013.01); H01L 21/7685 (2013.01); H01L 23/53238 (2013.01)

(57)ABSTRACT

A method for selectively depositing graphene on a metal surface in a back-end-of-line substrate is provided. The method comprises providing the substrate comprising a first dielectric layer and a copper interconnect in the first dielectric layer, the copper interconnect having an exposed metal surface, wherein the exposed metal surface comprises copper, and selectively deposing a carbon layer on the exposed metal surface.

